

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4163	257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.	US-PGPUB; USPAT	OR	OFF	2005/03/02 16:31
L2	0	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and ((gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os)) same ((plug interconnect wiring trace via contact) with (copper cu)) same (source drain))	US-PGPUB; USPAT	OR	ON	2005/03/02 16:32
L3	17	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and (polysilicon with gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os))	US-PGPUB; USPAT	OR	ON	2005/03/02 16:32
L4	21	((gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os)) same ((plug interconnect wiring trace via contact) with (copper cu)) same (source drain))	US-PGPUB; USPAT	OR	ON	2005/03/02 16:57
L5	40	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and (gate same ((plug interconnect wiring trace via contact) with (copper cu)) same (source drain))	US-PGPUB; USPAT	OR	ON	2005/03/02 17:15
L6	18	(gate with ((plug contact) near2 (copper cu)) with (source drain))	US-PGPUB; USPAT	OR	ON	2005/03/02 17:26
L7	33	438/620.ccls. and ((plug contact) with (copper cu))	US-PGPUB; USPAT	OR	ON	2005/03/02 17:28
L8	1	((insulat\$4 dielectric oxide dioxide nitride interlayer) with (silicon si)) and ((unit adj cell) (lattice near4 (constant mismatch\$4 match\$4))) and ((atom\$2 near (radius radii)) (bond\$4 near energy))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 17:32
L9	35	((atom\$2 near (radius radii)) (bond\$4 near energy)) and (semiconductor silicon si wafer substrate) and (copper cu) and (rhodium rh ruthenium ru iridium ir osmium os platinum pt)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 17:33

L10	8	(semiconductor silicon si wafer substrate) and ((interconnect\$5 metal\$1is\$7 metal\$1iz\$7) same ((platinum pt) near4 (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer"))) same ((osmium os) with (palladium pd cobalt co nickel ni titanium ti) with (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer")))	US-PGPUB; USPAT	OR	ON	2005/03/02 17:35
L11	300	((atom\$2 near (radius radii)) (bond\$4 near energy)) and (semiconductor silicon si wafer substrate) and ((copper cu) same (rhodium rh ruthenium ru iridium ir osmium os platinum pt) same (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer")))	US-PGPUB; USPAT	OR	ON	2005/03/02 17:39
L12	148	((insulat\$4 dielectric oxide dioxide nitride interlayer) with (silicon si)) and ((unit adj cell) (lattice near4 (constant mismatch\$4 match\$4)) (atom\$2 near (radius radii)) (bond\$4 near energy)) and ((film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer") with (conduct\$5 platinum pt copper cu silver ag gold au rhodium rh ruthenium ru iridium ir osmium os palladium pd cobalt co nickel ni titanium ti))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 18:04
L13	640	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and ((copper cu silver ag gold au platinum pt) same ((rhodium rh ruthenium ru iridium ir osmium os platinum pt) with (palladium pd cobalt co nickel ni titanium ti)))	US-PGPUB; USPAT	OR	ON	2005/03/02 18:07
L14	260	(semiconductor silicon si wafer substrate) and ((insulat\$4 dielectric oxide dioxide nitride interlayer) with (silicon si)) and ((unit adj cell) (lattice near4 (constant mismatch\$4 match\$4))) and ((atom\$2 near (radius radii)) (bond\$4 near energy))	US-PGPUB; USPAT	OR	ON	2005/03/02 18:07

L15	426	(semiconductor silicon si wafer substrate) and ((interconnect\$5 metal\$1is\$7 metal\$1iz\$7) same ((copper cu silver ag gold au) near4 (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer"))) same ((rhodium rh ruthenium ru iridium ir osmium os platinum pt) with (palladium pd cobalt co nickel ni titanium ti) with (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer") with (element constituent consist\$3 compris\$3 atom metal)))	US-PGPUB; USPAT	OR	ON	2005/03/02 18:18
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